

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

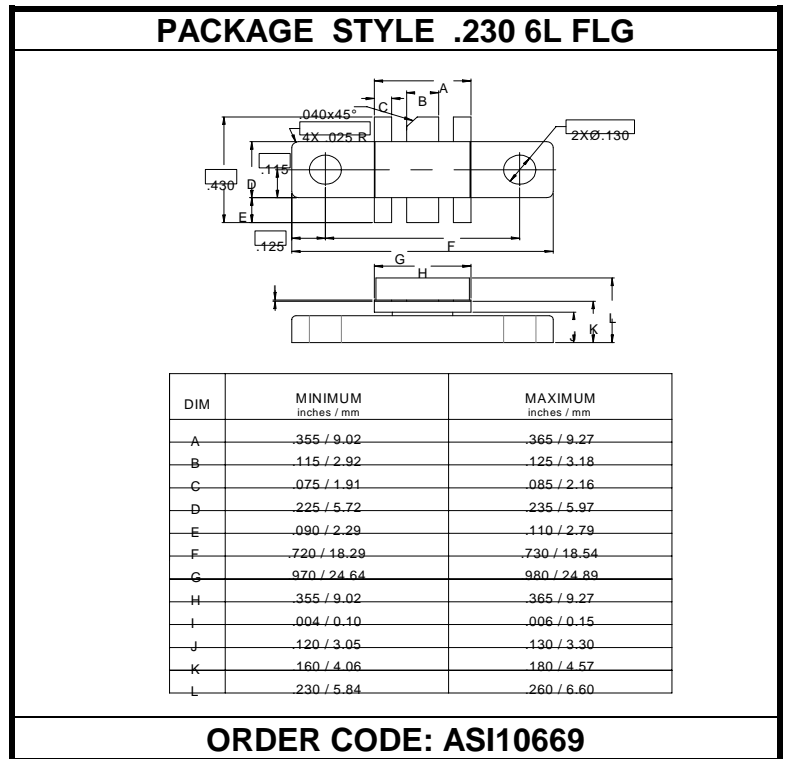
The **ASI UHBS15-2** is Designed for Class C, FM Base Station Applications up to 960 MHz.

FEATURES:

- Internal Input Matching Network
- $P_G = 9.0$ dB at 15 W/960 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	2.0 A
V_{CBO}	55 V
V_{CEO}	28 V
V_{CES}	55 V
V_{EBO}	4.0 V
P_{DISS}	50 W @ $T_C = 25$ °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	3.0 °C/W


CHARACTERISTICS $T_C = 25$ °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 50$ mA	28			V
BV_{CES}	$I_C = 50$ mA $R_{BE} = 10$ Ω	55			V
BV_{EBO}	$I_E = 10$ mA	4.0			V
I_{CBO}	$V_{CB} = 15$ V			2.5	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 1.0$ A	30		200	---
C_{ob}	$V_{CB} = 24$ V $f = 1.0$ MHz			25	pF
P_G η_c	$V_{CE} = 24$ V $P_{OUT} = 15$ W $f = 960$ GHz	9.5	50		dB %